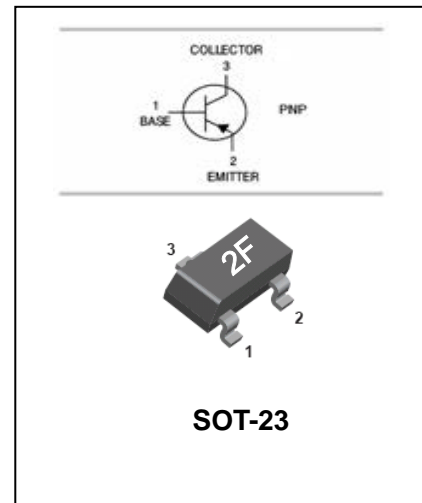


## FEATURES

- Epitaxial planar die construction.
- Complementary NPN type available MMBT2222A.
- Ideal for medium power amplification and switching.
- MSL 1

## APPLICATIONS

- This device is designed as a general purpose amplifier and switching.
- The useful dynamic range extends to 600mA as a switch and to 100MHz as a amplifier.



## MAXIMUM RATING @ Ta=25°C unless otherwise specified

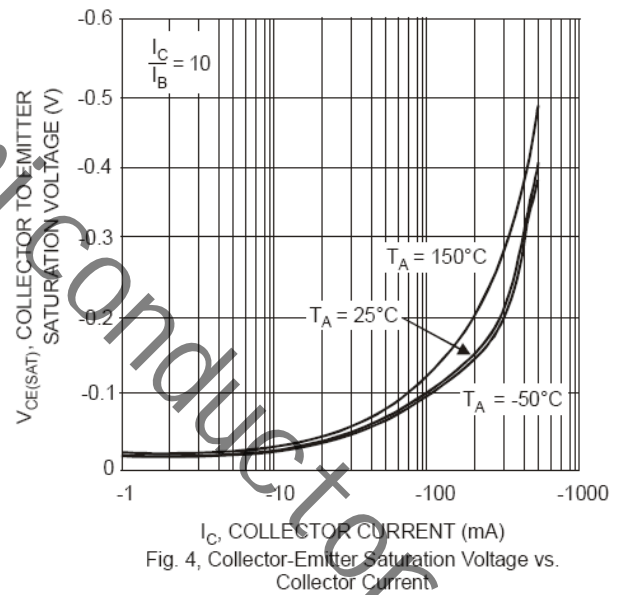
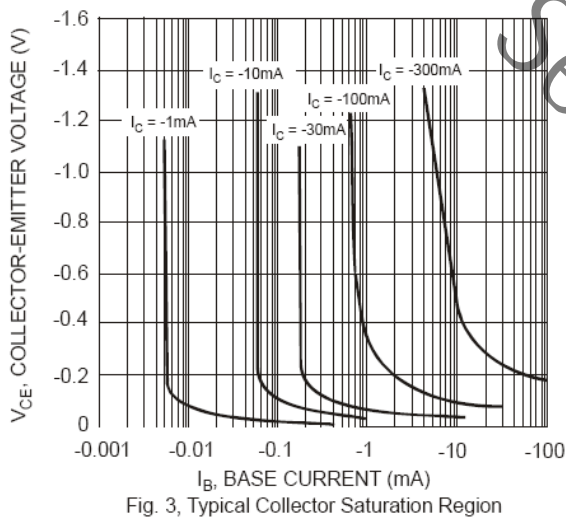
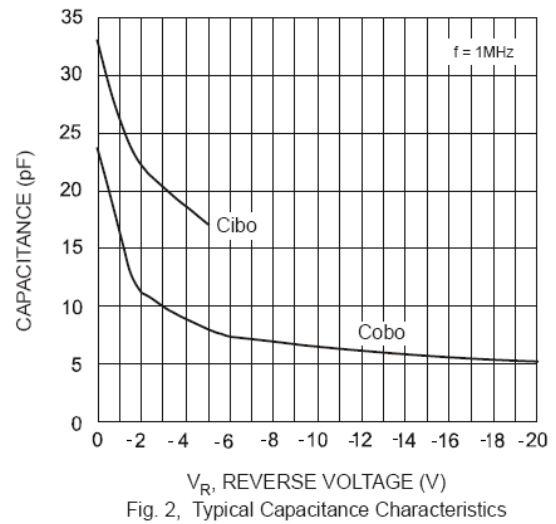
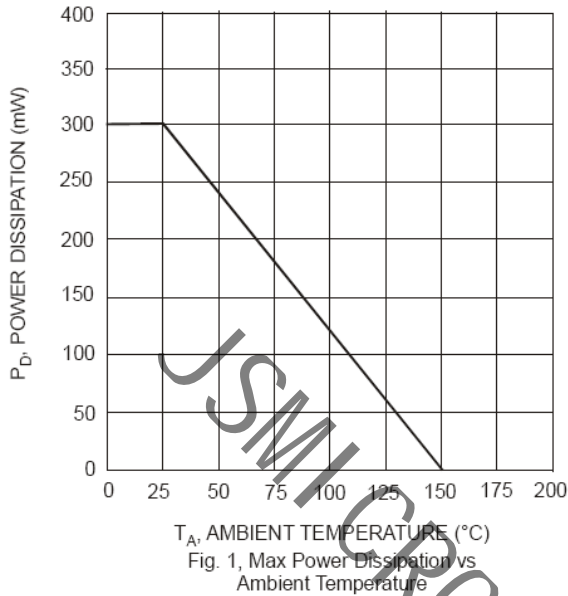
Symbol	Parameter	Value	Unit
V <sub>CB0</sub>	Collector-Base Voltage	-60	V
V <sub>CEO</sub>	Collector-Emitter Voltage	-60	V
V <sub>EBO</sub>	Emitter-Base Voltage	-5	V
I <sub>C</sub>	Collector Current -Continuous	-600	mA
P <sub>D</sub>	Total Device Dissipation	300	mW
R <sub>θJA</sub>	Thermal Resistance Junction to Ambient	417	°C/W
R <sub>θJC</sub>	Thermal Resistance Junction to Case	250	°C/W
T <sub>J</sub> , T <sub>STG</sub>	Junction and Storage Temperature	-55 to +150	°C/W

## ESD RATING

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	C

## ELECTRICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = -10\mu A$ $I_E = 0$	-60		V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -10mA$ $I_B = 0$	-60		V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -10\mu A$ $I_C = 0$	-5		V
Collector cut-off current	$I_{CBO}$	$V_{CB} = -50V$ $I_E = 0$ $V_{CB} = -50V$ $I_E = 0$ $T_A = 125^\circ C$		-10 -10	nA $\mu A$
Collector cut-off current	$I_{CEX}$	$V_{CE} = -30V$ , $V_{BE(OFF)} = -0.5V$		-50	nA
Base cut-off current	$I_{BL}$	$V_{CE} = -30V$ , $V_{BE(OFF)} = -0.5V$		-50	nA
DC current gain	$h_{FE}$	$V_{CE} = -10V$ $I_C = -100\mu A$ $V_{CE} = -10V$ $I_C = -1mA$ $V_{CE} = -10V$ $I_C = -10mA$ $V_{CE} = -10V$ $I_C = -150mA$ $V_{CE} = -10V$ $I_C = -500mA$	75 100 100 100 50	- - - 300 -	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -150mA$ $I_B = -15mA$ $I_C = -500mA$ $I_B = -50mA$		-0.4 -1.6	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = -150mA$ $I_B = -15mA$ $I_C = -500mA$ $I_B = -50mA$		-1.3 -2.6	V
Transition frequency	$f_T$	$V_{CE} = -20V$ $I_C = -50mA$ $f = 100MHz$	200		MHz
Output Capacitance	$C_{obo}$	$V_{CB} = -10V$ $f = 100kHz$ $I_E = 0$	-	8.0	pF
Input Capacitance	$C_{ibo}$	$V_{EB} = -2V$ $f = 100kHz$ $I_C = 0$	-	30	pF
Delay time	$t_d$	$V_{CE} = -30V$ , $I_C = -150mA$ ,		10	ns
Rise time	$t_r$	$I_{B1} = -15mA$		40	ns
Storage time	$t_s$	$V_{CE} = -6V$ , $I_C = -150mA$		225	ns
Fall time	$t_f$	$I_{B1} = -I_{B2} = -15mA$		60	ns

**TYPICAL CHARACTERISTICS @  $T_a=25^\circ\text{C}$  unless otherwise specified**


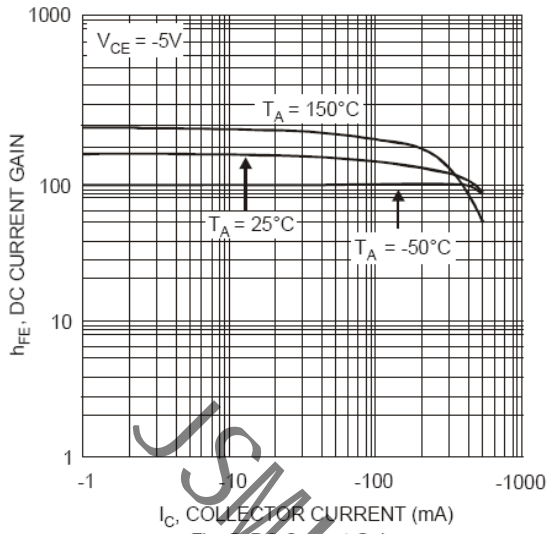


Fig. 5. DC Current Gain vs Collector Current

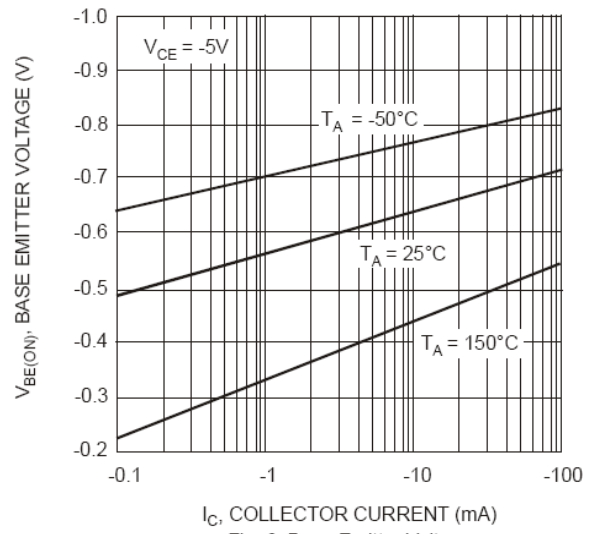


Fig. 6. Base-Emitter Voltage vs. Collector Current

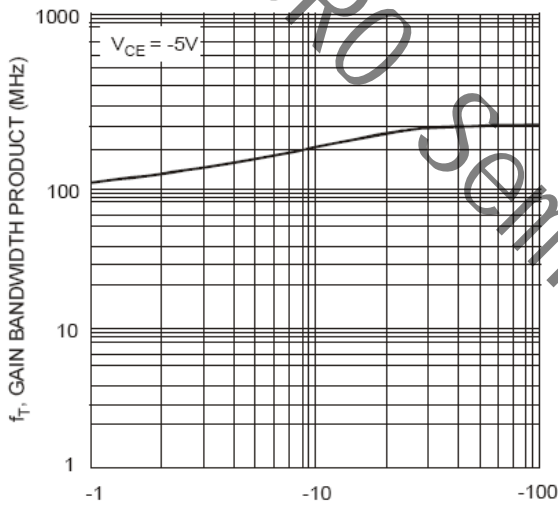
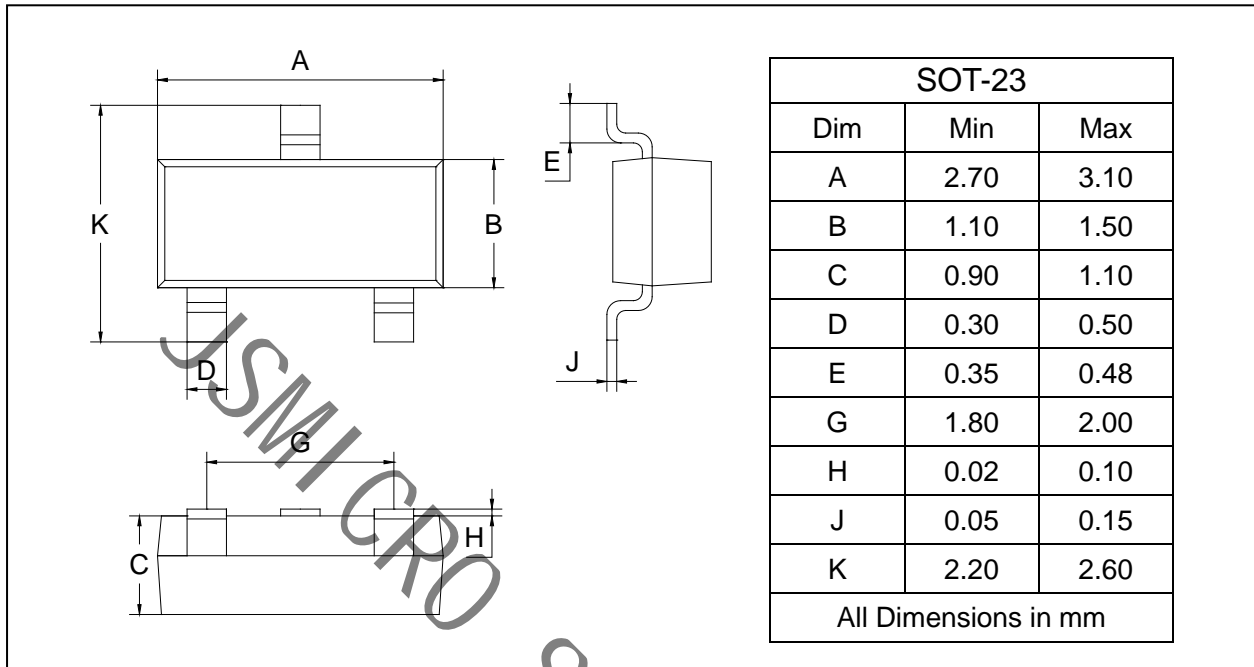


Fig. 7. Gain Bandwidth Product vs. Collector Current

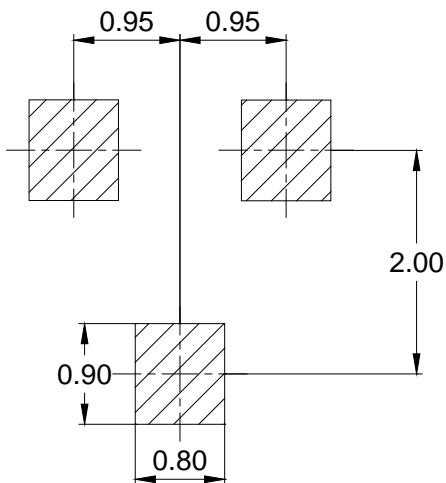
## PACKAGE OUTLINE

Plastic surface mounted package

SOT-23



## SOLDERING FOOTPRINT



## PACKAGE INFORMATION

Device	Package	Shipping
MMBT2907A	SOT-23	3000 pcs / Tape & Reel

单击下面可查看定价，库存，交付和生命周期等信息

[>>JSMSEMI\(杰盛微\)](#)